

PNP Silicon Transistor

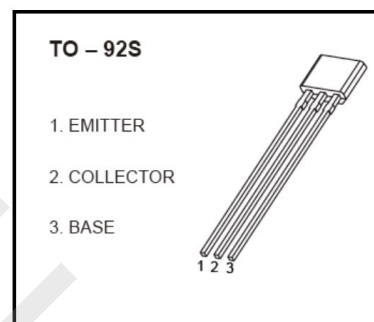
2SA1048

Features

- Complementary to: 2SC2458
- Package: TO-92S

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	-50	V
Collector-emitter voltage	BV_{CEO}	-50	V
Emitter-base voltage	BV_{EBO}	-5	V
Collector current	I_{CM}	-150	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~+150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -100\mu A, I_C = 0$	-5			V
collector-base cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
collector-emitter cut-off current	I_{CEO}	$V_{CE} = -50V, I_B = 0$			-0.1	μA
emitter-base cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	H_{FE}	$V_{CE} = -6V, I_C = -2mA$	70		400	
collector-emitter saturation voltage	V_{CESAT}	$I_C = -100mA, I_B = -10mA$			-0.3	V
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			7	pF
Transition frequency	f_T	$V_{CE} = -10V, I_C = -1mA$	80			MHz

H_{FE} Classification

Rank	O	Y	GR
Range	70-140	120-240	200-400